



# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · High Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 1500V(Min)
- · High Switching Speed
- · High Reliability
- Built-in Damper Diode
- · Good Linearity of hFE
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

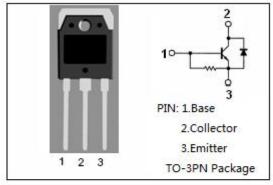


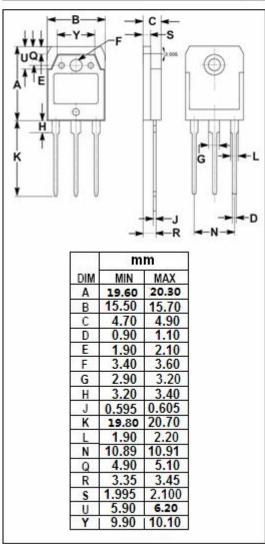
### **APPLICATIONS**

· Ultrahigh-definition color display horizontal deflection output applications

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous 6		Α	
Іср	Collector Current-Peak	16	А	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	3.0 W		
	Collector Power Dissipation @ T <sub>C</sub> =25℃	50	VV	
Тл	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	







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2SC4294

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

Tc=25 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.1A; I <sub>B</sub> = 0	800			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 5A; I <sub>B</sub> = 1.2A			5.0	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1.2A			1.5	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μА		
Ices	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			1.0	mA		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0	40		130	mA		
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	8					
h <sub>FE-2</sub>	DC current gain	Ic= 5A; V <sub>CE</sub> = 5V	4		6			
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 6A			2.0	V		
Switching times								
t <sub>stg</sub>	Storage Time	Ic= 5A, I <sub>B1</sub> = 1A; I <sub>B2</sub> = -2A;			3.0	μs		
t <sub>f</sub>	Fall Time	V <sub>cc</sub> = 200V			0.3	μ <b>s</b>		

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